
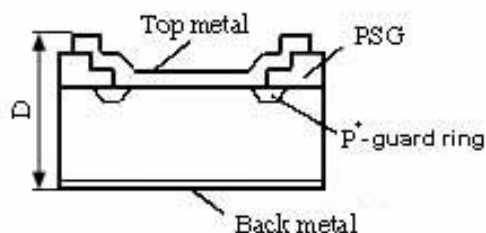
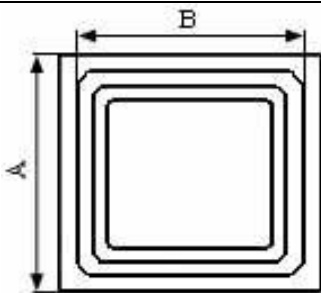


		10A/40V. Die Size-115mil.		
				
Electrical Characteristics	Symbol	Unit	Spec. limit	Die Sort
Breakdown Voltage @ $I_R=10\text{mA}$	V_{BR}	V	40	45
Average Rectified Forward Current	$I_{F(AV)}$	A	10,0	-
DC Forward Voltage @ 25°C, $I_F=10,0\text{A}$; @ 25°C, $I_F=20,0\text{A}$;	V_F	V	0,49 0,56	0,47 0,54
Maximum Reverse Current @ 25°C, $V_R=45\text{V}$ @ 25°C, $V_R=40\text{V}$ @ 125°C, $V_R=40\text{V}$	I_R	mA	- 0,130 65,0	0,130 0,100 60,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	I_{FSM}	A	200	-
Peak Repetitive Reverse Surge Current @ 2,0µs, f=1kHz., $T_J<150^\circ\text{C}$.	I_{RRM}	A	4,5	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV	±8 (contact)	
Voltage Rate of Change	dV/dt	V/µS	10.000	
Operating Junction Temperature	T_J	°C	150	



DIM	ITEM	µm
A_x A_y	Wafer Form Die Size	2920 2920
B_x B_y	Top Metal Size	2780 2780
D	Thickness	300max.
Scribe line Width		80

Top metal:

- a) Al – for Wire Bonding;
- b) Al-Ni-Ag – for Soldering.

Backside metal: **Ti-Ni-Ag.**